## 1. Product profile

### 1.1 General description

Passivated sensitive gate triac in a SOT78 plastic package.

### 1.2 Features

- Very sensitive gate
- Direct interfacing to logic level ICs


### 1.3 Applications

■ General purpose switching and phase
230 V lamp dimmers control

### 1.4 Quick reference data

- $\mathrm{V}_{\text {DRM }} \leq 600 \mathrm{~V}$ (BT138-600D)
- $\mathrm{V}_{\text {DRM }} \leq 600 \mathrm{~V}$ (BT138-600E)
- $\mathrm{V}_{\text {DRM }} \leq 800 \mathrm{~V}$ (BT138-800E)
- $\mathrm{I}_{\mathrm{GT}} \leq 5 \mathrm{~mA}$ (BT138-600D)
- $\mathrm{I}_{\mathrm{GT}} \leq 10 \mathrm{~mA}(\mathrm{BT} 138-600 \mathrm{E})$
- $\mathrm{I}_{\mathrm{GT}} \leq 10 \mathrm{~mA}(\mathrm{BT} 138-800 \mathrm{E})$
- Gate triggering in four quadrants

■ Direct interfacing to low power gate drive circuits

- $\mathrm{I}_{\mathrm{T} \text { (RMS) }} \leq 12 \mathrm{~A}$
- $\mathrm{I}_{\text {TSM }} \leq 95 \mathrm{~A}$ ( $\left.\mathrm{t}=20 \mathrm{~ms}\right)$
- $\mathrm{I}_{\mathrm{GT}} \leq 10 \mathrm{~mA}(\mathrm{~T} 2-\mathrm{G}+)(\mathrm{BT} 138-600 \mathrm{D})$
- $\mathrm{I}_{\mathrm{GT}} \leq 25 \mathrm{~mA}(\mathrm{~T} 2-\mathrm{G}+)$ (BT138-600E)
- $\mathrm{I}_{\mathrm{GT}} \leq 25 \mathrm{~mA}(\mathrm{~T} 2-\mathrm{G}+)(\mathrm{BT} 138-800 \mathrm{E})$


## 2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
| :--- | :--- | :--- | :--- |
| 1 | main terminal $1(\mathrm{~T} 1)$ |  |  |

## 3. Ordering information

Table 2. Ordering information

| Type number | Package |  |  |
| :--- | :--- | :--- | :--- | :--- |
|  | Name | Description | Version |
| BT138-600D | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead | SOT78 |
| BT138-600E |  | TO-220AB |  |
| BT138-800E |  |  |  |

## 4. Limiting values

Table 3. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {DRM }}$ | repetitive peak off-state voltage |  |  |  |  |
|  |  | BT138-600D | [1] - | 600 | V |
|  |  | BT138-600E | [1] - | 600 | V |
|  |  | BT138-800E | - | 800 | V |
| $\mathrm{I}_{\text {(RMS) }}$ | RMS on-state current | full sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 99^{\circ} \mathrm{C}$; see Figure 4 and $\underline{5}$ | - | 12 | A |
| $I_{\text {TSM }}$ | non-repetitive peak on-state current | full sine wave; $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ prior to surge; see Figure 2 and $\underline{3}$ |  |  |  |
|  |  | $\mathrm{t}=20 \mathrm{~ms}$ | - | 95 | A |
|  |  | $\mathrm{t}=16.7 \mathrm{~ms}$ | - | 105 | A |
| 12 t | ${ }^{2} \mathrm{t}$ for fusing | $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$ | - | 45 | $A^{2} \mathrm{~S}$ |

Table 3. Limiting values ...continued In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{dl}_{\mathrm{T}} / \mathrm{dt}$ | rate of rise of on-state current | $\begin{aligned} & \mathrm{I}_{\mathrm{TM}}=20 \mathrm{~A} ; \mathrm{I}_{\mathrm{G}}=0.2 \mathrm{~A} ; \\ & \mathrm{d} \mathrm{I}_{\mathrm{G}} / \mathrm{dt}=0.2 \mathrm{~A} / \mathrm{\mu s} \end{aligned}$ |  |  |  |
|  |  | T2+ G+ | - | 50 | A/ $\mu \mathrm{s}$ |
|  |  | T2+ G- | - | 50 | A/ $\mu \mathrm{s}$ |
|  |  | T2- G- | - | 50 | A/ $\mu \mathrm{s}$ |
|  |  | T2-G+ | - | 10 | A/ $\mu \mathrm{s}$ |
| $\mathrm{I}_{\mathrm{GM}}$ | peak gate current |  | - | 2 | A |
| $\mathrm{P}_{\mathrm{GM}}$ | peak gate power |  | - | 5 | W |
| $\mathrm{Pa}_{\mathrm{G}(\mathrm{AV})}$ | average gate power | over any 20 ms period | - | 0.5 | W |
| $\mathrm{T}_{\text {stg }}$ | storage temperature |  | -40 | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | - | 125 | ${ }^{\circ} \mathrm{C}$ |

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed $15 \mathrm{~A} / \mu \mathrm{s}$.


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

$\mathrm{f}=50 \mathrm{~Hz}$
Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values


Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values


Fig 4. RMS on-state current as a function of surge duration; maximum values


Fig 5. RMS on-state current as a function of mounting base temperature; maximum values

## 5. Thermal characteristics

Table 4. Thermal characteristics
$\left.\begin{array}{lllllcc}\hline \text { Symbol } & \text { Parameter } & \text { Conditions } & \text { Min } & \text { Typ } & \text { Max } & \text { Unit } \\ \hline R_{\text {th(j-mb) }} & \begin{array}{llll}\text { thermal resistance from junction to } \\ \text { mounting base }\end{array} & \text { full cycle; see Figure 6 }\end{array}\right)$


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 6. Static characteristics

Table 5. Static characteristics
$T_{j}=25^{\circ} \mathrm{C}$ unless otherwise specified.

| Symbol | Parameter | Conditions | BT138-600D |  |  | $\begin{aligned} & \text { BT138-600E } \\ & \text { BT138-800E } \end{aligned}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typ | Max | Min | Typ | Max |  |
| $I_{\text {GT }}$ | gate trigger current | $\begin{aligned} & \mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A} ; \\ & \text { see Figure } 8 \end{aligned}$ |  |  |  |  |  |  |  |
|  |  | T2+ G+ | - | 1.3 | 5 | - | 2.5 | 10 | mA |
|  |  | T2+ G- | - | 2.8 | 5 | - | 4.0 | 10 | mA |
|  |  | T2- G- | - | 3.2 | 5 | - | 5.0 | 10 | mA |
|  |  | T2-G+ | - | 5.5 | 10 | - | 11 | 25 | mA |
| $\mathrm{I}_{\mathrm{L}}$ | latching current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{G}}=0.1 \mathrm{~A} ;$ $\text { see Figure } 10$ |  |  |  |  |  |  |  |
|  |  | T2+ G+ | - | - | 15 | - | - | 30 | mA |
|  |  | T2+ G- | - | - | 20 | - | - | 40 | mA |
|  |  | T2- G- | - | - | 15 | - | - | 30 | mA |
|  |  | T2-G+ | - | - | 20 | - | - | 40 | mA |
| $\mathrm{I}_{\mathrm{H}}$ | holding current | $\begin{aligned} & \mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{G}}=0.1 \mathrm{~A} ; \\ & \text { see Figure } 11 \end{aligned}$ | - | - | 10 | - | - | 30 | mA |
| $\mathrm{V}_{T}$ | on-state voltage | $\mathrm{I}_{\mathrm{T}}=15 \mathrm{~A}$; see Figure 9 | - | 1.4 | 1.65 | - | 1.4 | 1.65 | V |
| $\mathrm{V}_{\mathrm{GT}}$ | gate trigger voltage | $\mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A}$; see Figure 7 |  |  |  |  |  |  |  |
|  |  | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V}$; | - | 0.7 | 1.5 | - | 0.7 | 1.5 | V |
|  |  | $\mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\text {DRM }} ; \mathrm{T}_{\mathrm{j}}=125^{\circ} \mathrm{C}$ | 0.25 | 0.4 | - | 0.25 | 0.4 | - | V |
| $\mathrm{I}_{\mathrm{D}}$ | off-state current | $\begin{aligned} & V_{D}=V_{\text {DRM }}(\max ) ; \\ & \mathrm{T}_{\mathrm{j}}=1255^{\circ} \mathrm{C} \end{aligned}$ | - | 0.1 | 0.5 | - | 0.1 | 0.5 | mA |

## 7. Dynamic characteristics

Table 6. Dynamic characteristics

| Symbol | Parameter | Conditions | BT138-600D |  |  | BT138-600E BT138-800E |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{dV} / \mathrm{D}^{\text {d }}$ dt | rate of rise of off-state voltage | $V_{D M}=0.67 \times V_{D R M(\max )} ;$ exponential waveform; gate open circuit; $\mathrm{T}_{\mathrm{j}}=110^{\circ} \mathrm{C}$ | - | 50 | - | - | 150 | - | V/ $/ \mathrm{s}$ |
| $\mathrm{tgt}_{\mathrm{gt}}$ | gate-controlled turn-on time | $\begin{aligned} & \mathrm{I}_{\mathrm{TM}}=16 \mathrm{~A} ; \\ & \mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\mathrm{DRM}(\max )} ; \\ & \mathrm{I}_{\mathrm{G}}=0.1 \mathrm{~A} ; \mathrm{dl}_{\mathrm{G}} / \mathrm{dt}=5 \mathrm{~A} / \mu \mathrm{s} \end{aligned}$ | - | 2 | - | - | 2 | - | $\mu \mathrm{s}$ |



Fig 7. Normalized gate trigger voltage as a function of junction temperature

(1) T2- G+
(2) T2- G-
(3) $\mathrm{T} 2+\mathrm{G}-$
(4) T2+ G+

Fig 8. Normalized gate trigger current as a function of junction temperature


Fig 9. On-state current as a function of on-state voltage


Fig 10. Normalized latching current as a function of junction temperature


Fig 11. Normalized holding current as a function of junction temperature

## 8. Package outline

| UNIT | $\mathbf{A}$ | $\mathbf{A}_{\mathbf{1}}$ | $\mathbf{b}$ | $\mathbf{b}_{\mathbf{1}}$ | $\mathbf{c}$ | $\mathbf{D}$ | $\mathbf{D}_{\mathbf{1}}$ | $\mathbf{E}$ | $\mathbf{e}$ | $\mathbf{L}$ | $\mathbf{L}_{\mathbf{1}}$ | $\mathbf{L}_{\mathbf{2}}$ <br> $\mathbf{m a x}$. | $\mathbf{p}$ | $\mathbf{q}$ | $\mathbf{Q}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 4.7 | 1.40 | 0.9 | 1.45 | 0.7 | 16.0 | 6.6 | 10.3 | 2.54 | 15.0 | 3.30 | 3.0 | 3.8 | 3.0 | 2.6 |
|  | 4.1 | 1.25 | 0.6 | 1.00 | 0.4 | 15.2 | 5.9 | 9.7 |  | 12.8 | 2.79 | 3.0 | 3.5 | 2.7 | 2.2 |


| OUTLINE <br> VERSION | REFERENCES |  |  |  | EUROPEAN | ISSUE DATE |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  |  |  |
| SOT78 | IEC | JEDEC | JEITA |  | - | - |

Fig 12. Package outline SOT78 (TO-220AB)

## 9. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| :---: | :---: | :---: | :---: | :---: |
| BT138_SER_D_E_2 | 20080312 | Product data sheet | - | BT138_SERIES_E_1 |
| Modifications: | - The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. <br> - Legal texts have been adapted to the new company name where appropriate. <br> - BT138-600D product added |  |  |  |
| BT138_SERIES_E_1 | 19970901 | Product data sheet | - | - |

## 10. Legal information

### 10.1 Data sheet status

| Document status $\underline{[1][2]}$ | Product status[] | Definition |
| :--- | :--- | :--- |
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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## 12. Contents

1 Product profile ..... 1
1.1 General description ..... 1
1 Features ..... 1
1.3 Applications ..... 1
1.4 Quick reference data ..... 1
2 Pinning information ..... 2
3 Ordering information ..... 2
4 Limiting values ..... 2
5 Thermal characteristics ..... 5
6 Static characteristics. ..... 6
7 Dynamic characteristics ..... 7
8 Package outline ..... 9
9 Revision history. ..... 10
10 Legal information ..... 11
10.1 Data sheet status ..... 11
10.2 Definitions. ..... 11
10.3 Disclaimers ..... 11
10.4 Trademarks ..... 11
11 Contact information ..... 11
12 Contents ..... 12

